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FACSIMILE COVER SHEET

To: Examiner Tu-Tu Ho

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Transmission Date:

July 1, 2005

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Bao, et al.

Docket No.:

TSM03-0927

Serial No:

10/800,510

Art Unit:

2818

Date Filed:

March 15, 2004

Title:

Semiconductor Device Having a Second Level of Metallization Formed over a

First Level with Minimal Damage to the First Level and Method

## CERTIFICATION OF FACSIMILE TRANSMISSION

I hereby certify that the following papers are being transmitted by facsimile to the U.S. Patent and Trademark Office at 703-872-9306 on the date shown above:

- Certification of Facsimile Transmission (1 page)
- Response to Office Action (12 pages), to include:
  - Amendment (11 pages)
  - Drawing Sheet for New Figure 2g (1 page)

Respectfully submitted,

Legal Assistant

Confirmation Respectfully Requested

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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For:

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over a First Level with Minimal Damage to the First Level and Method

Mail Stop: Amendment Commissioner for Patents

P. O. Box 1450

Alexandria, VA 22313-1450

## **AMENDMENT**

Dear Sir:

The following amendments and remarks are presented in response to the Examiner's

Office Action mailed April 1, 2005. Please amend the above-referenced application as follows.